



60V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C (Note 5)
60V	$3.1 \text{m}\Omega$ @ V _{GS} = 10V	100A
600	4.5mΩ @ V _{GS} = 4.5V	100A

Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Low Rds(ON) Minimizes Power Losses
- Low Q_g Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMTH6004LPSWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Primary switches in isolated DC-DC
- Synchronous rectifiers
- Load switches

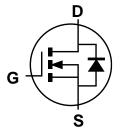
Mechanical Data

- Package: PowerDI[®]5060-8
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.097 grams (Approximate)

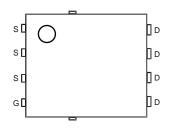
PowerDI5060-8/SWP (Type UX)



Top View Bottom View



Internal Schematic



Top View Pin Configuration

Ordering Information (Note 4)

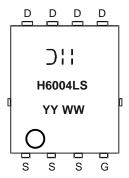
Part Number	Packago	Packing		
Fait Number	Package	Qty.	Carrier	
DMTH6004LPSWQ-13	PowerDI5060-8/SWP (Type UX)	2,500	Tape & Reel	

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.
- Limited by package.



Marking Information



O | | = Manufacturer's Marking H6004LS = Product Type Marking Code YYWW = Date Code Marking YY = Year Code (ex: 23 = 2023) WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		VDSS	60	V
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current (Note 6)	T _A = +25°C T _A = +70°C	I _D	22 16	А
Continuous Drain Current (Notes 5 & 7)	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	lo	100 100	А
Maximum Continuous Body Diode Forward Current (Note 6)		ls	100	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	400	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		Ism	400	Α
Avalanche Current, L = 0.2mH		las	40	Α
Avalanche Energy, L = 0.2mH		Eas	160	mJ

Thermal Characteristic

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	T _A = +25°C	PD	2.6	W
Thermal Resistance, Junction to Ambient (Note 6)	Reja	47	°C/W	
Total Power Dissipation (Note 7)	PD	138	W	
Thermal Resistance, Junction to Case (Note 7)		R _{θJC}	0.9	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

Notes:

- 5. Limited by package.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 7. Thermal resistance from junction to soldering point (on the exposed drain pad).



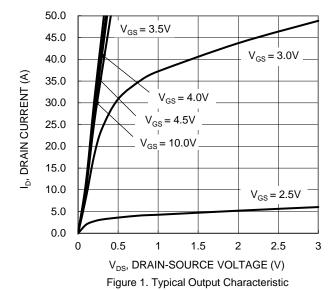
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BVDSS	60	_	_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μA	V _{DS} = 48V, V _{GS} = 0V	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	Vgs(TH)	1	_	3	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	D	_	2.5	3.1	mΩ	$V_{GS} = 10V, I_D = 25A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	3.3	4.5	mΩ	$V_{GS} = 4.5V, I_D = 20A$	
Diode Forward Voltage	VsD	_	_	1.3	V	V _G S = 0V, I _S = 25A	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss	_	5399	_		V _{DS} = 30V, V _{GS} = 0V f = 1MHz	
Output Capacitance	Coss	_	1306	_	pF		
Reverse Transfer Capacitance	Crss	_	92	_			
Gate Resistance	Rg	_	0.64	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 10V)	Qg	_	78.3	_		V _{DD} = 30V, I _D = 25A	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	38.5	_	nC		
Gate-Source Charge	Qgs	_	10.2	_	nc nc		
Gate-Drain Charge	Q_{gd}	_	20.4	_			
Turn-On Delay Time	tD(ON)	_	9.9	_		$V_{DD} = 30V, V_{GS} = 10V$ $I_{D} = 25A, R_{g} = 3.5\Omega$	
Turn-On Rise Time	t _R	_	17.7	_			
Turn-Off Delay Time	tD(OFF)	_	53.5	_	ns		
Turn-Off Fall Time	t _F	_	32.9	_			
Body Diode Reverse Recovery Time	t _{RR}	_	49.7	_	ns	1 054 41/41 4004/-	
Body Diode Reverse Recovery Charge	Q _{RR}	_	78.9	_	nC	I _F = 25A, dl/dt = 100A/µs	

Notes:

^{8.} Short duration pulse test used to minimize self-heating effect. 9. Guaranteed by design. Not subject to production testing.





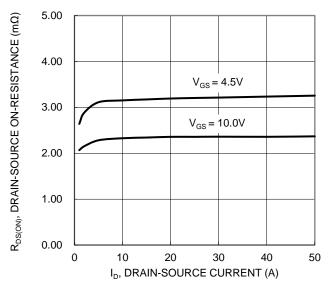


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

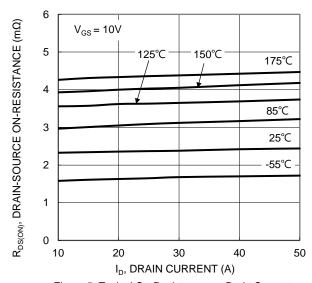


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

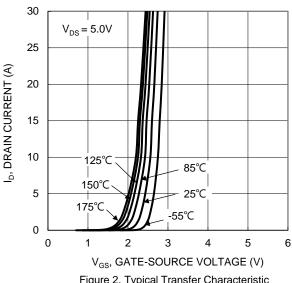


Figure 2. Typical Transfer Characteristic

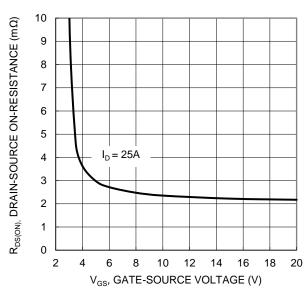


Figure 4. Typical Transfer Characteristic

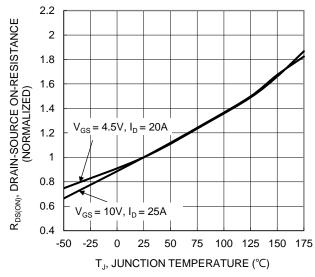


Figure 6. On-Resistance Variation with Temperature





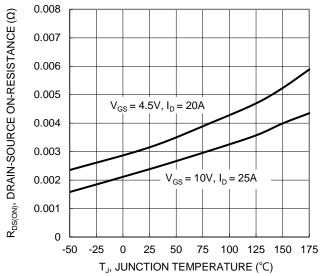


Figure 7. On-Resistance Variation with Temperature

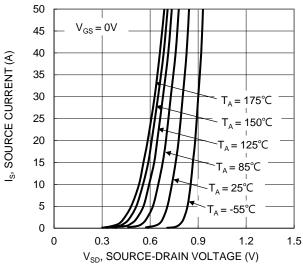


Figure 9. Diode Forward Voltage vs. Current

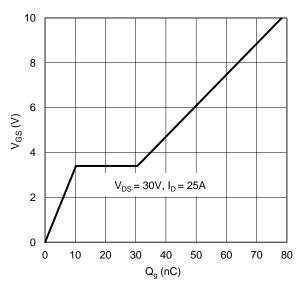


Figure 11. Gate Charge

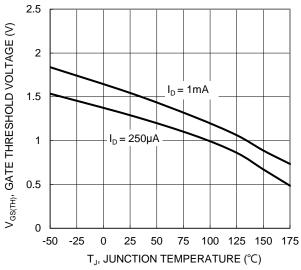


Figure 8. Gate Threshold Variation vs. Temperature

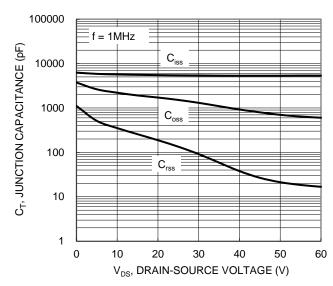


Figure 10. Typical Junction Capacitance

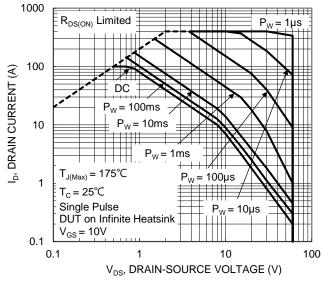


Figure 12. SOA, Safe Operation Area



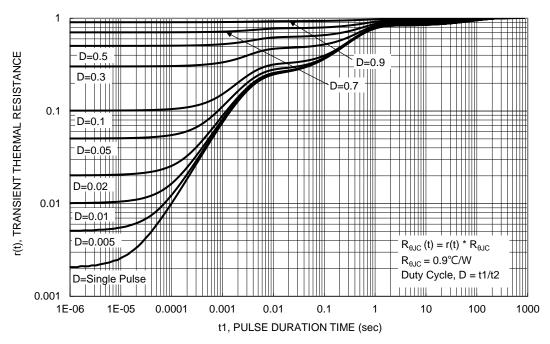


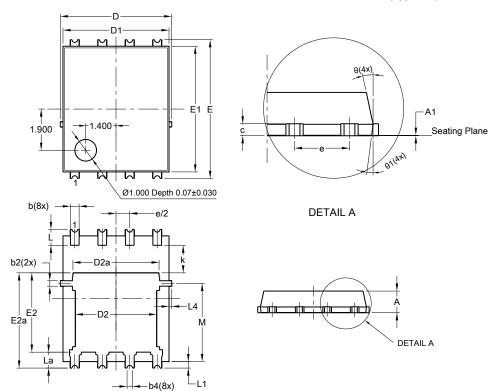
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8/SWP (Type UX)

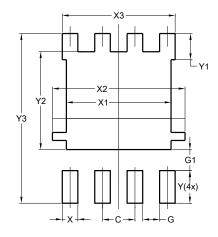


Ро	PowerDI5060-8/SWP (Type UX)			
Dim	Min Max		Тур	
Α	0.90	1.10	1.00	
A1	0	0.05		
b	0.30	0.50	0.41	
b2	0.20	0.35	0.25	
b4	().25REF	=	
C D	0.230	0.330	0.277	
	5	.15 BS0	2	
D1	4.70	5.10	4.90	
D2	3.56	3.96	3.76	
D2a	3.78	4.18	3.98	
Е	6	.40 BS0)	
E1	5.60	6.00	5.80	
E2	3.46	3.86	3.66	
E2a	4.195	4.595	4.395	
е		.27BSC)	
k	1.05			
L	0.635	0.835	0.735	
La	0.635	0.835	0.735	
L1	0.200	0.400	0.300	
L1a	0.050REF			
L4	0.025	0.225	0.125	
М	3.205	4.005	3.605	
θ	10°	12°	11°	
θ1	6°	8°	7°	
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8/SWP (Type UX)



Dimensions	(in mm)		
С	1.270		
G	0.660		
G1	0.820		
X	0.610		
X1	4.100		
X2	5.190		
Х3	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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